

IN THE ABSTRACT:

Please cancel the current abstract and insert the following.

~~A mask is composed of a substrate, and a pattern having a transmission factor formed on the substrate by using a material, wherein an optical path length difference between light beams respectively passing the pattern and an area adjacent thereto is greater than $(m-1/8)\lambda$ and less than $(m+1/8)\lambda$, where λ is a wavelength of incident light, and m is an integer.~~

-- A projection exposure apparatus having an exposure mode for exposing a mask to transfer a pattern image of the mask onto a photosensitive substrate. The apparatus includes a light source for emitting an exposure beam, a projection optical system for receiving the exposure beam and for exposing a mask to transfer a pattern image of the mask onto a photosensitive substrate, wherein the mask includes (i) a substrate transparent for the exposure beam, and (ii) a member translucent for the exposure beam formed on the transparent substrate, the transmission factor of the translucent member being different from a transmission factor of the transparent substrate, wherein a difference between an optical path length of the exposure beam passing through the transparent substrate and the translucent member and an optical path length of the exposure beam passing through the transparent substrate and the space adjacent to the translucent member on the transparent substrate is greater than $(m-1/8)\lambda$ and less than $(m+1/8)\lambda$, where λ is a wavelength of the exposure beam and m is an integer.--